

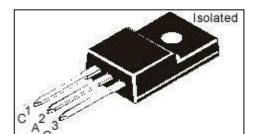


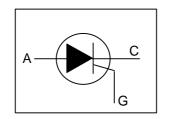




THYRISTORS

BT151X





TO-220FP Fully Isolated Plastic Package

For use in Applications Requiring High Bidirectional Blocking Voltage Capability and high Thermal Cycling Performance. Typical Applications include Motor Control, Industrial and Domestic Lighting, Heating and Static Switching.

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITION	VA	UNIT	
		BT151X-	500	650	
Repetitive Peak Off State Voltage	V_{DRM} , V_{RRM}		*500	*650	V
Average On State Current	I _{T (AV)}	half sine wave, T _{hs} ≤ 87°C	5.7		Α
RMS On State Current	I _{T (RMS)}	all conduction angles	9.0		Α
Non Repetitive Peak On State Current		half sine wave, T _J =25°C			
Non Repetitive Feak On State Current	I _{TSM}	prior to surge			
		t=10ms	1	00	Α
		t=8.3ms	110		Α
I ² t for Fusing	l ² t	t=10ms	50		A ² s
Repetitive Rate Of Rise of On State	dl _⊤ /dt	I _{TM} =20A, I _G =50mA,	50		Λ /
Current After Triggering	αι _Τ /αι	dl _G /dt=50mA/μs			A/μs
Peak Gate Current	I_{GM}		2.0		Α
Peak Gate Voltage	V_{GM}		5.0		V
Peak Reverse Gate Voltage	V_{RGM}		5.0		V
Peak Gate Power	P_GM		5.0		W
Average Gate Power	P _{G (AV)}	Over any 20ms period	0.5		W
Storage Temperature	T _{stg}		- 40 to +150		°C
Operating Junction Temperature	T _j		125		°C

ISOLATION LIMITING VALUE and CHARACTERISTIC (T_{hs}=25°C unless specified otherwise)

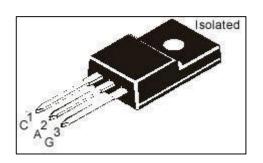
100 EATION Elimining VALUE and GHARAGTERIOTIO (1 hs-20 0 amics specified difference)								
PARAMETER	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT		
R.M.S Isolation Voltage from all three		f=50-60 Hz; sinusoidal						
terminals to external heatsink	V _{ISOL}	waveform; R.H. <u><</u> 65%;			2500	V		
		clean and dustfree						
Capacitance from T2 to external heatsink	C _{ISOL}	f=1MHz		10		pF		

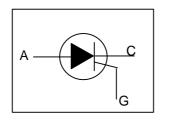
THERMAL RESISTANCE

Junction to Heatsink	R _{th (j-hs)} with heatsink compound		4.5 max	K/W
		without heatsink compound	6.5 max	K/W
Junction to Ambient	R _{th (j-a)}	in free air	55 typ	K/W

^{*}Although not recommended, off state voltage upto 800V may be applied without damage, but the thyristor may switch to the on state. The rate of rise of current should not exceed 15A/ms

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ELECTRICAL CHARACTERISTICS (T_J=25°C unless specified otherwise)

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PARAMETER	SYMBOL	TEST CONDITION	MIN	MAX	UNIT			
Gate Trigger Current	I _{GT}	V _D =12V, I _T =0.1A		15	mΑ			
Latching Current	ار	V _D =12V, I _{GT} =0.1A		40	mΑ			
Holding Current	I _H	$V_D=12V$, $I_{GT}=0.1A$		20	mΑ			
On State Voltage	V_{T}	I _T =23A		1.75	V			
Gate Trigger Voltage	V_{GT}	$V_D = 12V, I_T = 0.1A$		1.5	V			
		$V_D=V_{DRM}$ (max), $I_T=0.1A, T_J=125$ °C	0.25		٧			
Off State Leakage Current	I _{D,} I _R	$V_D = V_{DRM}$ (max), $V_R = V_{RRM}$ (max) $T_J = 125$ °C		0.5	mA			

DYNAMIC CHARACTERISTICS

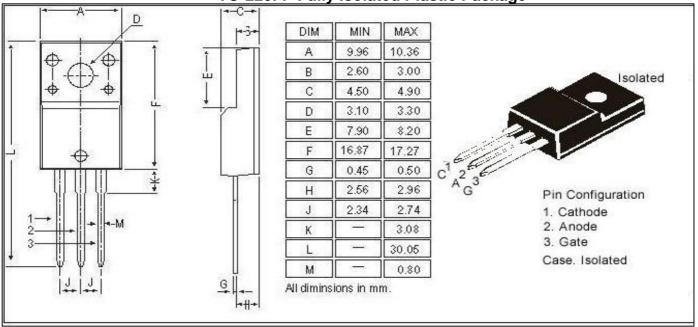
PARAMETER	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Critical Rate of Rise of Off State Voltage	dV _D /dt	V _{DM} =67% V _{DRM} =max, T _J =125°C, exponential waveform				
		gate open circuit	50			V/μs
		$R_{GK} = 100\Omega$	200			V/μs
Gate Controlled Turn On time	t _{gt}	I_{TM} =40A, V_D = V_{DRM} (max), I_G =0.1A, dI_G / dt =5A/ μ s		2.0		μs
Circuit Commutated Turn Off time	t _q	V_{DM} =67% V_{DRM} =(max), T_J =125°C, I_{TM} =20A, V_R =25V, dI_{TM} / dt =30A/ μ s, dV_D / dt =50V/ μ s, R_{GK} =100 Ω		70		μs

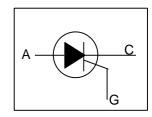
Marking	BT151X-500	BT151X-650
	CDXX	CDXX
	BT151X	BT151X
	- 500	- 650
XX=Date Code		

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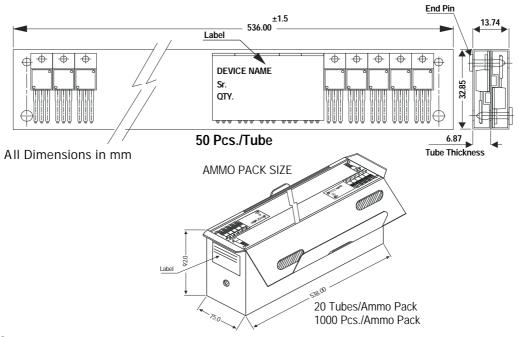
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TO-220 Tube Packing



Packing Detail

PACKAGE	STANDARD PACK		INNER CARTON BOX		OUTER CARTON BOX		
	Details	Net Weight /Qty	Size	Oty	Size Oty G		GrWt
TO-220 /FP	200 pcs/polybag	396 gm/200 pcs	3" x 7.5" x 7.5"	1.0K	17" x 15" x 13.5"	16.0K	36 kgs
	50 pcs/tube	120 gm/50 pcs	3.5" x 3.7" x 21.5"	1.0K	19" x 19" x 19"	10.0K	29 kgs

Notes BT151X

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Disclaimer

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CDIL is a registered Trademark of
Continental Device India Limited
C-120 Naraina Industrial Area, New Delhi 110 028, India.
Telephone + 91-11-2579 6150. 5141 1112 Fax + 91-11-2579 5290, 5141 1119
email@cdil.com www.cdilsemi.com

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